IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of: Sunkara et al.

Filed: November 10, 2003

Serial No: 10/705,687

For: BULK SYNTHESIS OF METAL AND METAL BASED DIELECTRIC NANOWIRES

Atty. Docket No.: AD138/2001

) Examiner:
) Group Art Unit:

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INFORMATION DISCLOSURE DOCUMENT

Enclosed is a list and copies of references considered by Applicant to be pertinent in the examination of the above-identified patent application.

Applicant submits this Information Disclosure Statement in accordance with the duty of disclosure under 37CFR §1.56 and 1.97-1.98. This Statement is filed in accordance with 37 CFR §1.97(b)(3), prior to issuance of a First Office.

Applicants(s) submitted herewith patents, publications or other information of which they are aware, which they believe may be material to the examination of this application and in respect

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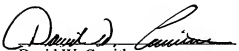
Respectfully submitted,



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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of

	Complete if Known
Application Number	10/705,687
Filing Date	November 10, 2003
First Named Inventor	Mahendra Sunkara
Art Unit	
Examiner Name	
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U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Examiner Initials*	Cite No.[1]	Foreign Patent Document Country Code[3] -Number[4]- Kind Code[5] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]
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Examiner Signature	/Edward M. Johnson/ (06/24/2007)	Date Considered	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. [1] Applicant's unique citation designation number (optional). [2] See Kinds Codes of US PTO Patent Documents at www.uspto.gov or MPEP 901.04. [3] Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4] For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5] Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6] Applicant is to place a check mark here if English language Translation is attached.